ABSTRACT OF THE DISCLOSURE

A semiconductor memory device according to the present invention includes a memory cell capacitor for storing data thereon. The capacitor is made up of a first electrode connected to a contact plug, a second electrode and a capacitive insulating film interposed between the first and second electrodes. The first electrode includes a first barrier film in contact with the contact plug and a second barrier film, which is formed on the first barrier film and prevents the diffusion of oxygen. The second barrier film covers the upper and side faces of the first barrier film.